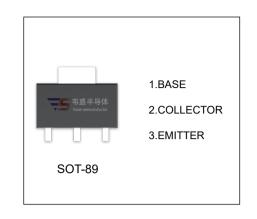


2SC4272 TRANSISTOR (NPN)

FEATURES

- Small Flat Package
- Large Current Capacity



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	75	V
V _{CEO}	Collector-Emitter Voltage	45	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current	1	Α
Pc	Collector Power Dissipation	500	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	250 °C/W	
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}$

ELECTRICAL CHARACTERISTICS (T_a =25 $^{\circ}$ C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =10μA,I _E =0	75			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA,I _B =0	45			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μA,I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =40V,I _E =0			1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V,I _C =0			1	μA
DC current gain	h _{FE}	V _{CE} =5V, I _C =500mA	60		320	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =500mA,I _B =50mA			0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =500mA,I _B =50mA			1.2	V
Transition frequency	f _T	VcE=10V,Ic=50mA	180			MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		15		pF

CLASSIFICATION OF h_{FE}

RANK	D	E	F	
RANGE	60 - 120	100 - 200	160-320	
MARKING	СН			